

High-reliability discrete products and engineering services since 1977

# 2N3879

## NPN SILICON POWER TRANSISTORS

### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

### **MAXIMUM RATINGS**

Ratings	Symbol	2N3879	Unit
Collector-Emitter Voltage	$V_{CEO}$	75	Vdc
Collector-Base Voltage	$V_{CBO}$	120	Vdc
Emitter-Base Voltage	$V_{EBO}$	7.0	Vdc
Base Current	I <sub>B</sub>	5.0	Adc
Collector Current	lc	7.0	Adc
Total Power Dissipation T <sub>A</sub> = 25°C (1)	P <sub>D</sub>	35	W
Operating & Storage Junction Temperature Range	T <sub>J</sub> ,T <sub>stg</sub>	-65 to +200	°C
Maximum Thermal Resistance Junction to Case	R <sub>ÐJC</sub>	5.0	°C/W

Note 1: Derate linearly @ 200mW/°C for T<sub>A</sub> > 25°C

### **ELECTRICAL CHARACTERSITICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage I <sub>C</sub> = 200 mA	V <sub>(BR)CEO</sub>	75	-	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 50 \text{ Vdc}$	I <sub>CEO</sub>	-	5.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 50 \text{ Vdc}, V_{BE} = 1.5 \text{ V}$	I <sub>CEX</sub>	-	4.0	mAdc
Collector-Base Cutoff Current V <sub>CB</sub> = 120 Vdc	Ісво	-	25	mAdc
Emitter-Base Cutoff Current V <sub>EB</sub> = 7.0 Vdc	ІЕВО		10	mAdc
Forward Current Transfer Ratio $I_C = 0.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}$ $I_C = 4.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}$ $I_C = 4.0 \text{ Adc, } V_{CE} = 2.0 \text{ Vdc}$	h <sub>FE</sub>	40 20 12	- 80 100	-
Collector-Emitter Saturation Voltage $I_C = 4.0 \text{ Adc}$ , $I_B = 0.4 \text{ Adc}$	V <sub>CE(sat)</sub>	-	1.2	Vdc
Base-Emitter Saturation Voltage $I_C = 4.0 \text{ Adc}$ , $I_B = 0.4 \text{ Adc}$	$V_{BE(sat)}$	-	2.0	Vdc
Base-Emitter On Voltage $I_C = 4.0 \text{ Adc}, V_{CE} = 2.0 \text{V}$	V <sub>BE(ON)</sub>		1.8	Vdc
DYNAMIC CHARACTERISTICS				
Magnitude of Common Emitter Small-Signal Short Circuit Forward Current Transfer Ratio $I_C=0.5\;\text{Adc},V_{CE}=4.0\;\text{Vdc},f=100\;\text{kHz}$	Ih <sub>FE</sub> I	4.0	20	-



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Characteristics	Symbol	Min.	Max.	Unit
Output Capacitance $V_{CB} = 10 \text{ Vdc, } I_E = 0, \ 100 \text{kHz} \le f \le 1.0 \text{MHz}$	Cobo	-	300	pF
SWITCHING CHARACTERISTICS				
Turn-On Time $V_{CC} = 30Vdc, I_C = 4.0 Adc, I_B = 40mAdc$	t <sub>on</sub>	-	0.44	μs
Turn-Off Time $V_{CC} = 30Vdc, I_C = 4.0 Adc, I_B = -I_B = 40 \text{mAdc}$	t <sub>off</sub>	-	1.2	μs

#### SAFE OPERATING AREA

#### Dc Tests

 $T_C = 25$ °C, 1 cycle, t = 1.0s

Test 1

 $V_{CE}$  = 5.0 Vdc,  $I_C$  = 7.0 Adc

Test 2

 $V_{CE} = 28 \text{ Vdc}$ ,  $I_C = 500 \text{ mAdc}$ 

Test 3

 $V_{CE}$  = 40 Vdc,  $I_C$  = 500 mAdc

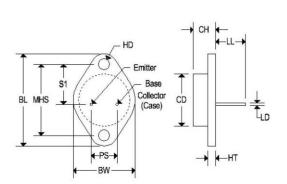
Test 4

 $V_{CE}$  = 75 Vdc,  $I_C$  = 100 mAdc

Note 1: Pulse Test: Pulse Width = 300µs, Duty Cycle ≤ 2.0%

### **MECHANICAL CHARACTERISTICS**

Case	TO-66
Marking	Alpha-numeric
Polarity	See below



	TO-66			
Dim	Inches		Millimeters	
	Min	Max	Min	Max
BL	1.205	1.280	30.60	32.50
CD	0.445	0.557	11.303	14.148
CH	0.257	0.284	6.540	7.220
LL	0.374	0.413	9.500	10.50
BW	0.680	0.727	17.26	18.46
LD	0.030	0.036	0.760	0.920
HT	0.054	0.065	1.380	1.650
MHS	0.951	0.976	24.16	24.78
S1	0.545	0.614	13.84	15.60
HD	0.131	0.154	3.320	3.920
PS	0.191	0.210	4.860	5.340